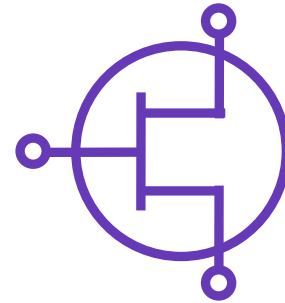


Model Features

- Broadband (DC to 30 GHz)
- Large-signal model (Modelithics-Enhanced Angelov)
- Measurement Validations:
 - Pulsed I-V (25 C to 85 C)
 - Multi-bias S-parameters (25C to 85C)
 - Load pull (25 C), 8 GHz
 - IP3 linearity validation, 8 GHz, 7 V 60%Idss
- Advanced model feature: enabling intrinsic I-V sensing.



MES-MWT-MWT11F-001
MwT-11F
Discrete GaAs MESFET

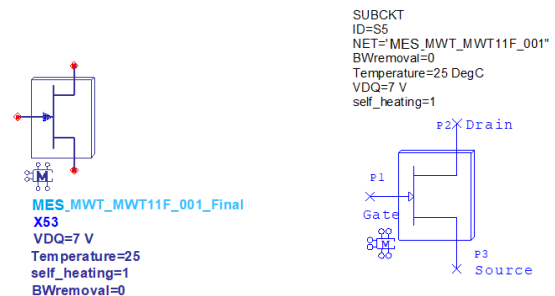
Model Description

The MES-MWT-MWT11F-001 is a non-linear model for the MwT-11F a discrete 2400 um GaAs MESFET (additional information is available at www.mwtinc.com). The model is based on the extraction of a customized Angelov non-linear model that is validated against the following Modelithics measurement data: I-V, S-parameters, load pull and IP3.

Technical Notes

- Model is optimized for 2, 4 and 7 V operation (209 mA (30% IDSS), 348 mA (50% IDSS) and 418 mA (60% IDSS)).
- Model Parameters:
 - **VDSQ**: For setting the optimum bias point of the model (default=7 V).
 - **Temperature**: represents the backside ambient temperature, validated at 25 C and 85 C.
 - **Self_heat**: switch for the electrothermal model (0 or 1), 0= self-heating is turned off, 1 (default)= self-heating is turned on.
 - **BWremoval**: 0 includes wire assembly (only used in measurements, 1 (default) sets model reference planes at the center of the gate, drain, and source bond pads.
 - [Modelithics Micro Probe Accessories](#) part number 0503, 5 mil Alumina adapter substrates were used to access the bond pads of discrete die.

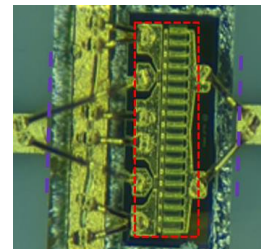
Model Representation



Keysight ADS

NI AWR

Reference Planes



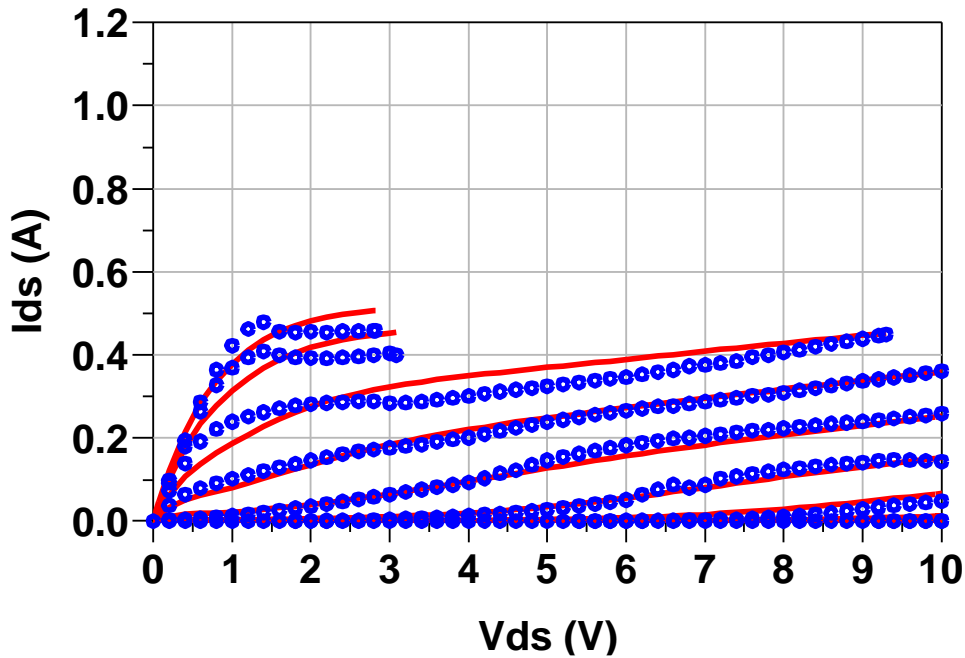
Model and Measurement Reference Planes (BWremoval=1)

Model and Measurement Reference Planes (BWremoval=0)

Model Simulation Settings

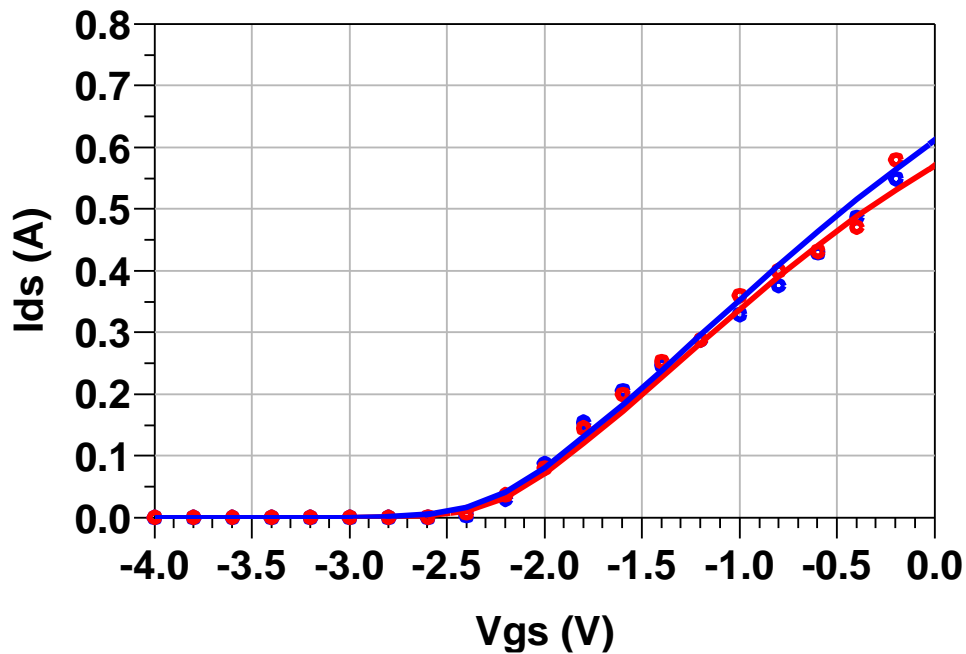
- **I-V**: self_heat: 0 for I-V simulations (self heating model turned OFF), Temperature=25 C
- **S-Parameters**: self_heat: 1 for CW bias, Temperature=25 C
- **Load Pull Single-tone and two tone validations**: self_heat: 1 for CW bias; Temperature=25 C.

DC I-V Characteristics: $V_{DSQ} = 7\text{ V}$, 25 C



Legend: Red Solid lines - Model data, O Symbols - Measured data
 Simulated at 25 C with V_{GS} varying from -4 to 0.2 V in steps of 0.4 V ,
 V_{DS} varying from 0 to 10 V in steps of 0.25 V . Model self_heat = 0 .

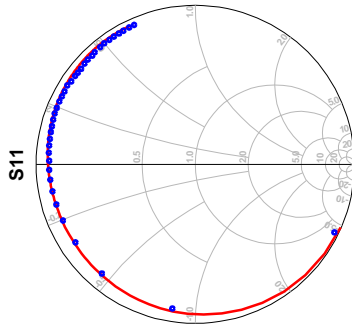
Model vs. Measurement Temperature IV Characteristics



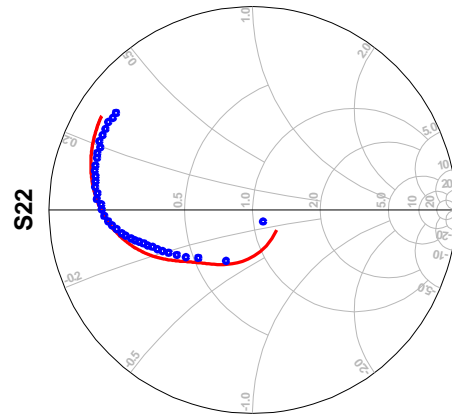
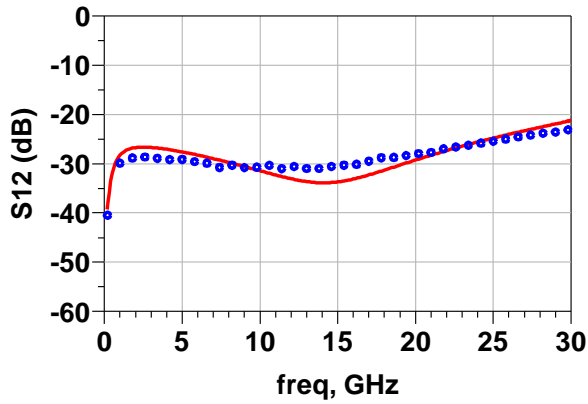
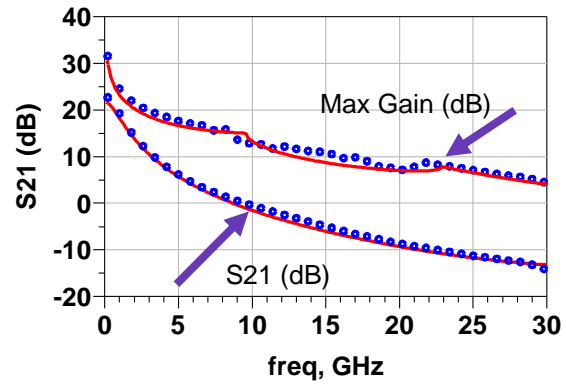
Legend: Red Solid lines: 85 C , Blue Solid lines: 25 C .
 Solid lines - Model data, Symbols - Measured data
 Simulated at 25 C and 85 C , V_{DSQ} of 7 V . Model self_heat = 0 .

S-Parameters Model vs. Measured:

VDS = 7 V, VGS = -0.74 V, IDS = 417.6 mA (60% IDSS), 25 C



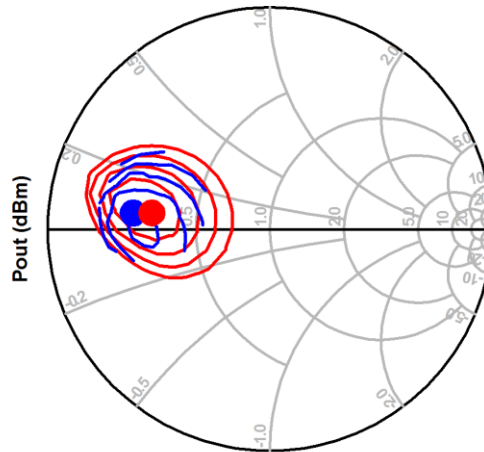
freq (200.0MHz to 30.00GHz)
freq (200.0MHz to 29.80GHz)



Legend: Red Solid lines - Model data, O Symbols - Measured data
 Simulated at 25 C with the frequency range from 0.2 – 30 GHz. 50 Ω Smith Charts
 BWremoval = 0

Load Pull Validation: Frequency = 8 GHz
 VDS = 7 V, VGS = -0.74 V, IDS = 417.6 mA (60% IDSS),
 Input Power = 23 dBm, Z0 = 50 Ω Center, 25 C

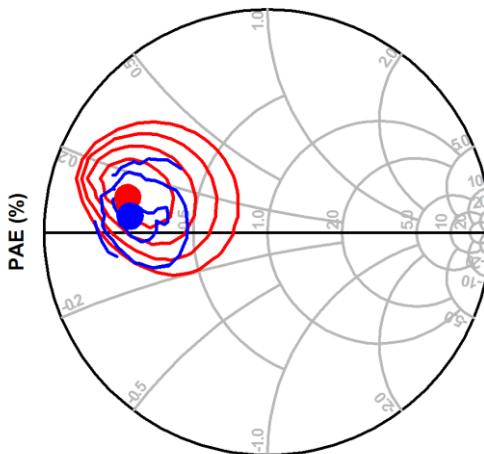
Power Tuning (0.5 dB contour step)



Test Bench Impedances (Ohms):

- ZS = 8.4 - j*2.7
- ZS2 = 10.0 + j*6.0
- ZS3 = 49.8 + j*28.1
- ZLoad2 = 19.1 + j*26.7
- ZLoad3 = 109.7 + j*22.7

Efficiency Tuning (5% contour step)



Legend: Red Solid lines – Model, Blue Solid lines – Measured, BWremoval = 0

| Load Pull Summary | Max Power Load Impedance (Ohms) | Max Power Value (dBm) | Max PAE Load Impedance (Ohms) | Max PAE Value (%) |
|-------------------|---------------------------------|-----------------------|-------------------------------|-------------------|
| Measured | 11.7 + j*2.8 | 31.8 | 11.7 + j*2.8 | 46.5 |
| Model | 15.1 + j*3.1 | 31.7 | 10.9 + j*5.9 | 48.1 |

Load pull data has been processed for contour display.

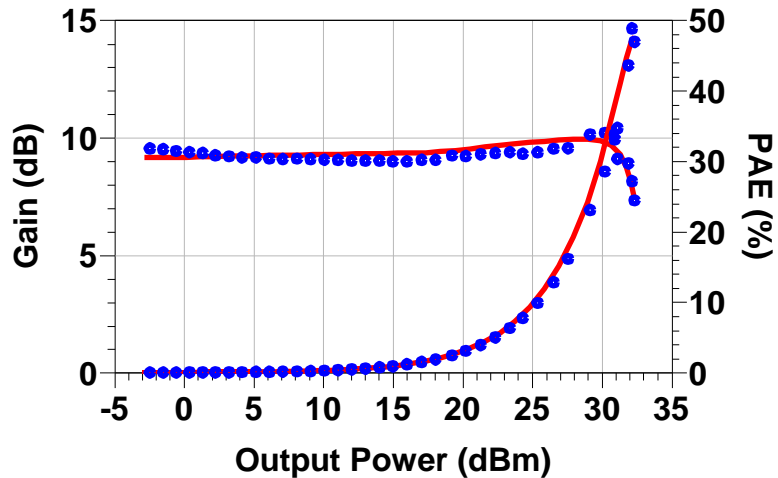
Single Tone Power Sweep: Frequency = 8 GHz
 VDS = 7 V, VGS = -0.74 V, IDS = 417.6 mA (60% IDSS), 25 C

Load Condition: Measured Power Tuned

Transducer Gain and Power Added Efficiency (PAE)

Load Condition: Power Tuned
 Test Bench Impedances
 (Ohms):

- ZS = 8.4 - j*2.7
- ZS2 = 10.0 + j*6.0
- ZS3 = 49.8 + j*28.1
- ZLoad = 13.6 + j*2.0
- ZLoad2 = 22.1 + j*27.7
- ZLoad3 = 112.5 + j*15.3



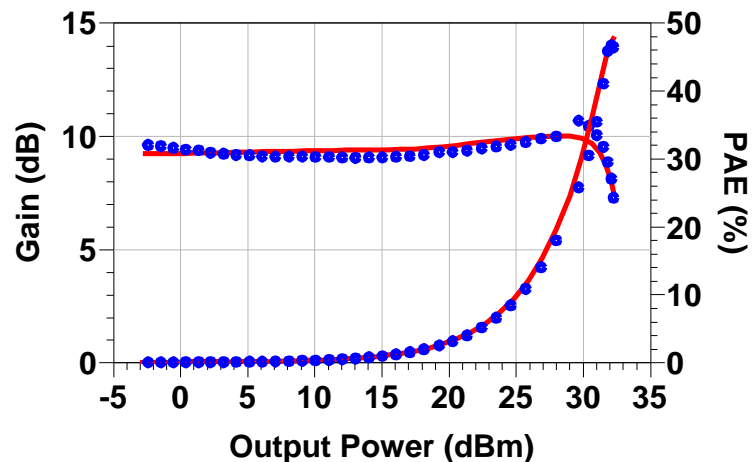
Legend: Red Solid lines - Model data, O Symbols - Measured data, BWremoval = 0

Load Condition: Measured PAE Tuned

Transducer Gain and Power Added Efficiency (PAE)

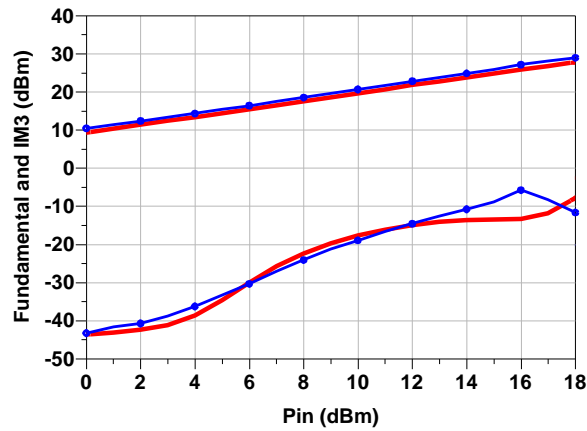
Load Condition: PAE Tuned
 Test Bench Impedances
 (Ohms):

- ZS = 8.4 - j*2.7
- ZS2 = 10.0 + j*6.0
- ZS3 = 49.8 + j*28.1
- ZLoad = 11.7 + j*2.8
- ZLoad2 = 19.1 + j*26.7
- ZLoad3 = 109.7 + j*22.7

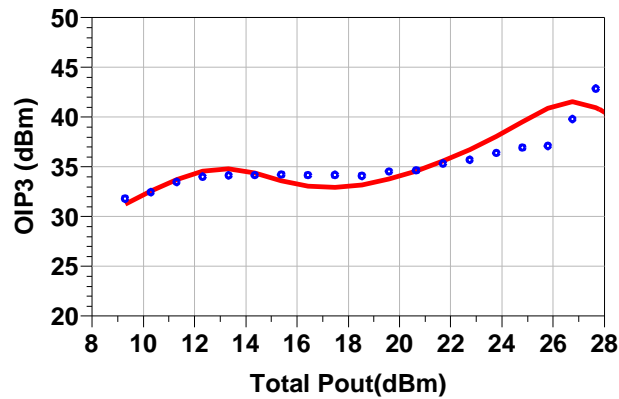


Legend: Red Solid lines - Model data, O Symbols - Measured data, BWremoval = 0

Two Tone Validation 8 GHz



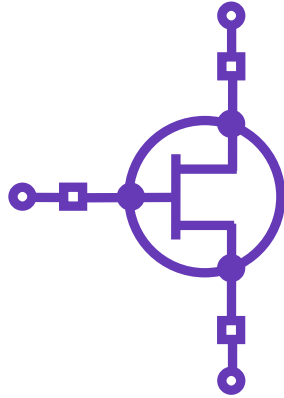
Simulated (solid line) and **measured (symbols)** tuned for max Power.
 Source impedance = $(8.8 - j*3.1)$ Ohms, load impedance = $(14.2 + j*3.1)$ Ohms.
 Frequency = 8 GHz, 5 MHz tone spacing, $V_{ds} = 7$ V, 417.6 mA (60% I_{dss})



Simulated (solid line) and **measured (symbols)** tuned for max Power.
 Source impedance = $(8.8 - j*3.1)$ Ohms, load impedance = $(14.2 + j*3.1)$ Ohms.
 Frequency = 8 GHz, 5 MHz tone spacing, $V_{ds} = 7$ V, 417.6 mA (60% I_{dss})

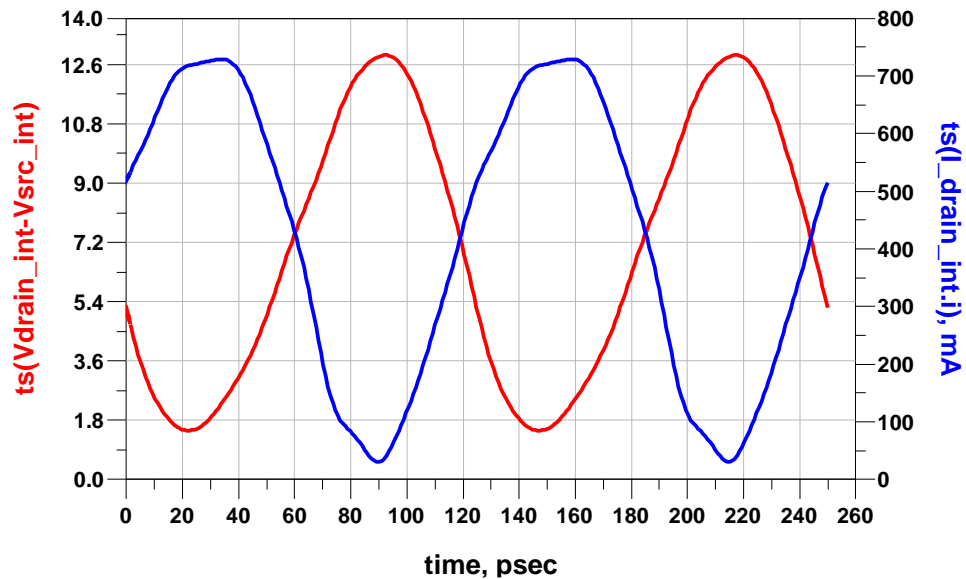
Advanced Model Features: Intrinsic Voltage/Current Sensing

Get Vds and Ids model data near current generator intrinsic planes while tuning.



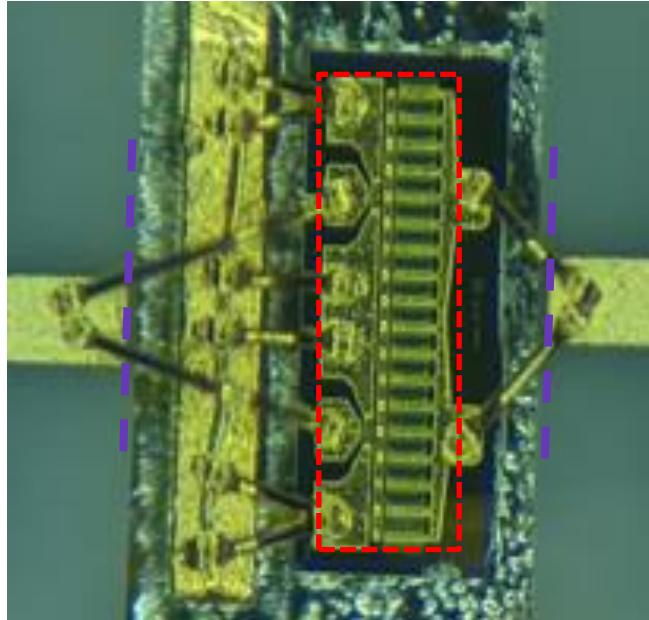
- External Model Planes
- Internal Model Planes for I/V waveform analysis
- Parasitic networks available separately from intrinsic I/V model

Example Plot of internal node Ids and Vds



Results based on harmonic balance simulation at 19 dBm input power, PAE matched at 8 GHz, 7 V, and 417.6 mA. $ZS = (8.4 - j*2.7)$ Ohms, $ZS2 = (10.0 + j*6.0)$ Ohms, $ZS3 = (49.8 + j*28.1)$ Ohms, $ZLoad = (13.6 + j*2.0)$ Ohms, $ZLoad2 = (22.1 + j*27.7)$ Ohms, $ZLoad3 = (112.5 + j*15.3)$ Ohms

Assembly Diagram



Test fixture details:

[Modelithics Micro Probe Accessories](#) part number 0503, 5 mil Alumina adapter substrates were used to access the bond pads of discrete die.

- Device thickness: 3.93 mil
- Test board thickness: 5 mil
- Bond-wire diameter: 1 mil gold
- Gate bond-wire length: 18 mil +/-2 (average)
- Drain bond-wire length: 12 mil +/-2 (average)
- Source bond-wire length (two wires per source pad): 8 mil +/-2 (average)
- Metal standoff external next to each source pad is 4 mil thick, its purpose is to shorten the bondwire lengths to the source/ground.
- Blue line is model planes with bondwires ON (BWremoval=0)
- Red line is model planes with bondwires OFF (BWremoval=1)

Model and Datasheet Revision Notes

| | |
|------------|--|
| 03/07/2023 | Original model and datasheet development |
| 06/21/2023 | Datasheet updated with IP3 validation |